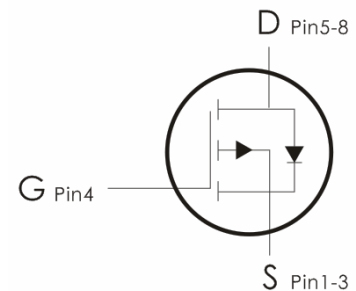
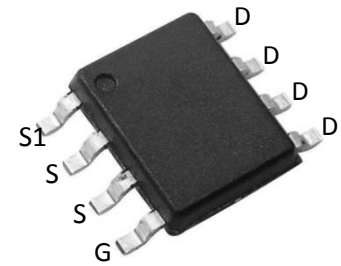


Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=-30V, I_D=-8A, R_{DS(ON)}<35m\Omega @V_{GS}=-10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_C=25^\circ\text{C}$	-8	A
	Pulsed Drain Current ¹	-30	
P_D	Power Dissipation	3.1	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ²	40	$^\circ\text{C}/\text{W}$

Electrical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	-30	-33	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=-30V, T_J=25^\circ\text{C}$	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics³						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	-1.3	-1.65	-2.5	V
$R_{DS(on)}$	Drain-Source On Resistance ²	$V_{GS}=-10V, I_D=-6.5A$	---	30	35	$\text{m}\Omega$
		$V_{GS}=-4.5V, I_D=-5A$	---	53	65	
G_{FS}	Forward Transconductance	$V_{DS}=-5V, I_D=-6.5A$	14	---	---	S
Dynamic Characteristics⁴						
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	660	---	μF
C_{oss}	Output Capacitance		---	100	---	
C_{rss}	Reverse Transfer Capacitance		---	65	---	
Switching Characteristics⁴						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=-15V, V_{GS}=-10V$ $I_D=-4A, R_{GEN}=3\ \Omega$	---	7.5	---	ns
t_r	Rise Time		---	5.5	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	19	---	ns
t_f	Fall Time		---	7	---	ns
Q_g	Total Gate Charge	$V_{DS}=-15V, V_{GS}=-10V,$ $I_D=-6.5A$	---	9.2	---	nC
Q_{gs}	Gate-Source Charge		---	1.6	---	nC
Q_{gd}	Gate-Drain "Miller" Charge		---	2.2	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage ³	$V_{GS}=0V, I_S=-8A, T_J=25^\circ\text{C}$	---	---	-1.2	V
I_S	Diode Forward Current ²	---	---	---	-8	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10\ \text{sec}$.
3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

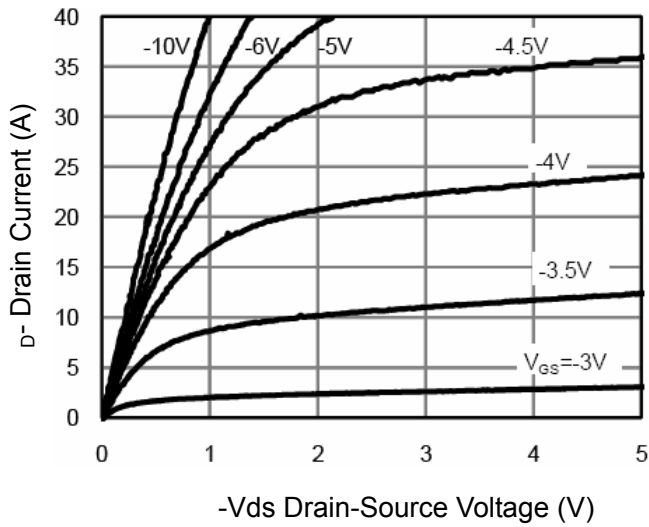


Figure 1 Output Characteristics

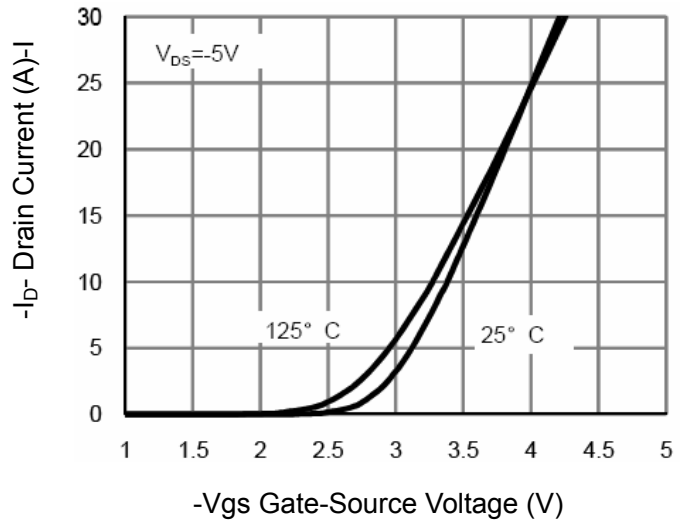


Figure 2 Transfer Characteristics

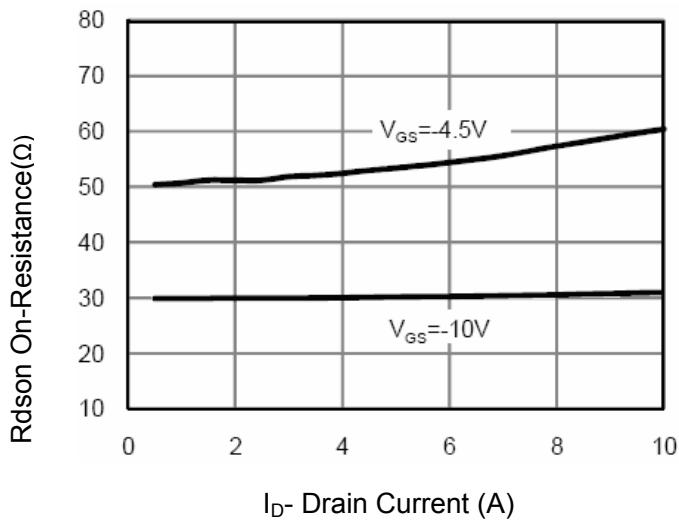


Figure 3 Rdson- Drain Current

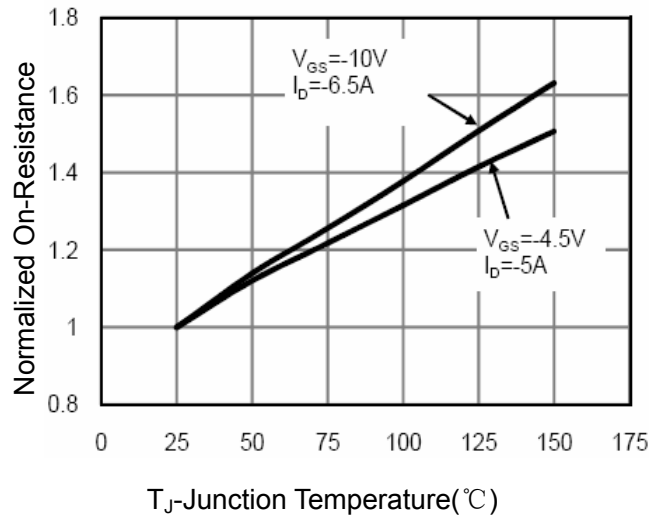


Figure 4 Rdson-Junction Temperature

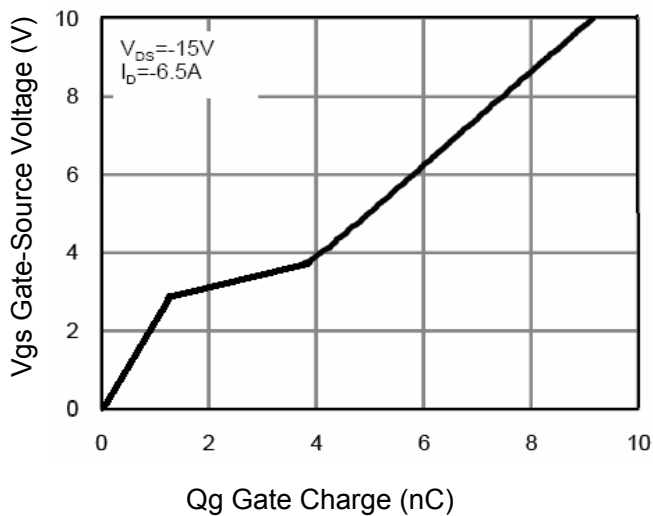


Figure 5 Gate Charge

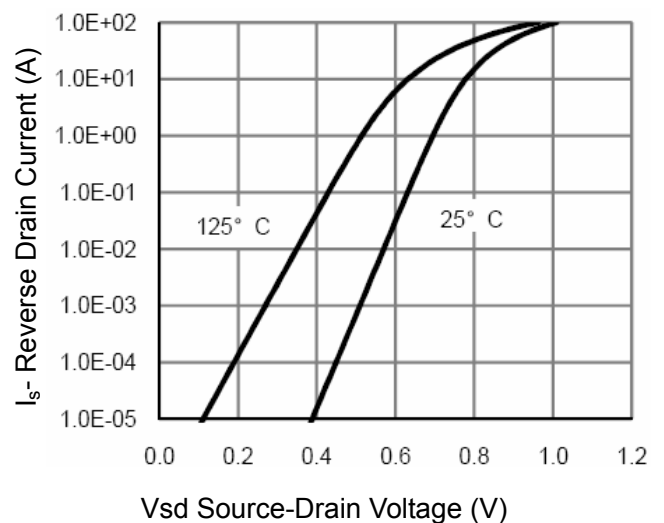
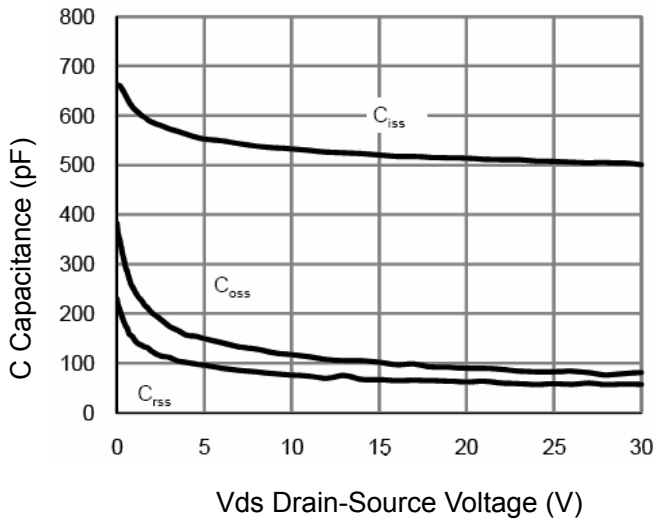
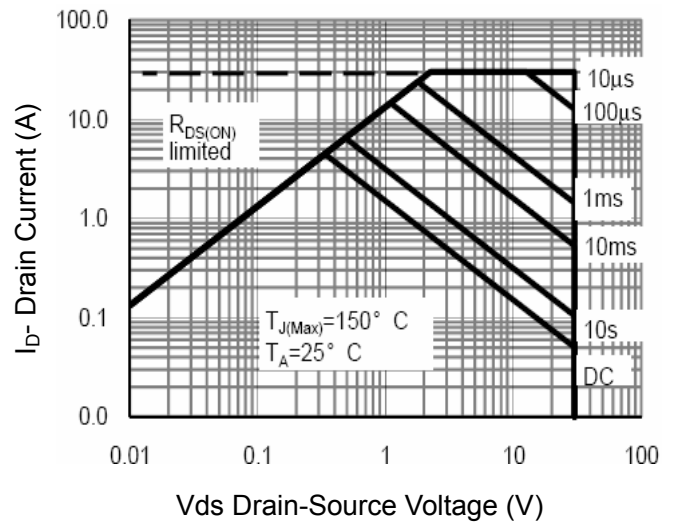
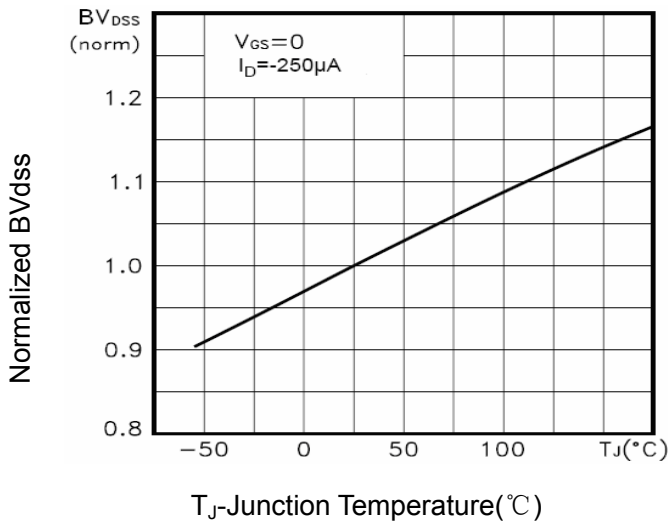
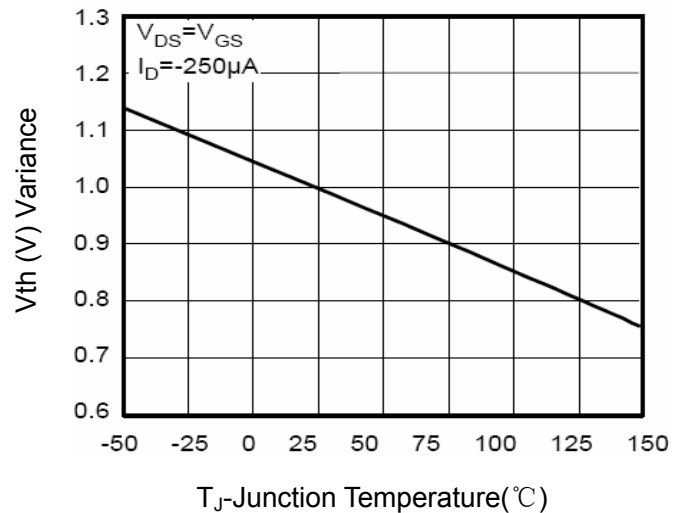
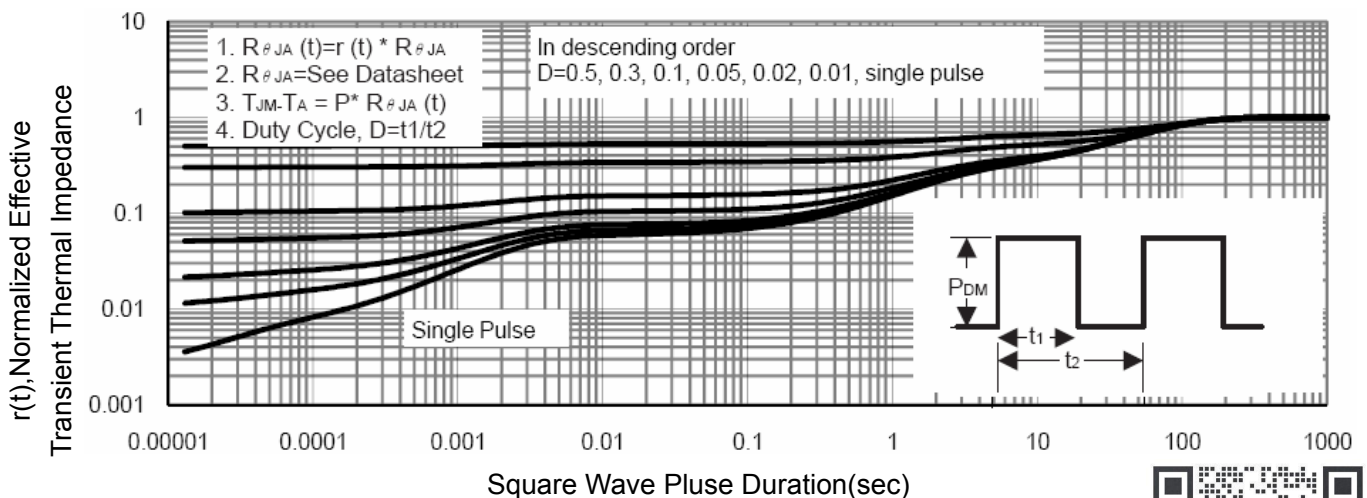


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 8 Safe Operation Area

Figure 9 BV_{DSS} vs Junction Temperature

Figure 10 V_{GS(th)} vs Junction Temperature

Figure 11 Normalized Maximum Transient Thermal Impedance
